

MMBC1623L7

NPN EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

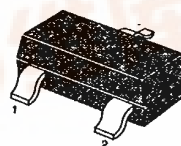
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	50	V
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EB0}	5.0	V
Collector Current	I_c	100	mA
Collector Dissipation	P_c	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBC1623L3 for graphs

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 40\text{V}$, $I_E = 0$		100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$		100	nA
DC Current Gain	β_{FE}	$V_{CE} = 6\text{V}$, $I_C = 1.0\text{mA}$	300	600	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100\text{mA}$, $I_B = 10\text{mA}$		0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 100\text{mA}$, $I_B = 10\text{mA}$		1.0	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C = 1.0\text{mA}$, $V_{CE} = 6\text{V}$	0.6	0.7	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = 6\text{V}$, $I_E = 10\text{mA}$ $f = 100\text{MHz}$	200		MHz

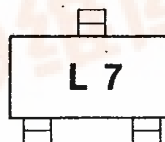
SOT-23



1. Base 2. Emitter 3. Collector

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Marking



SAMSUNG SEMICONDUCTOR

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